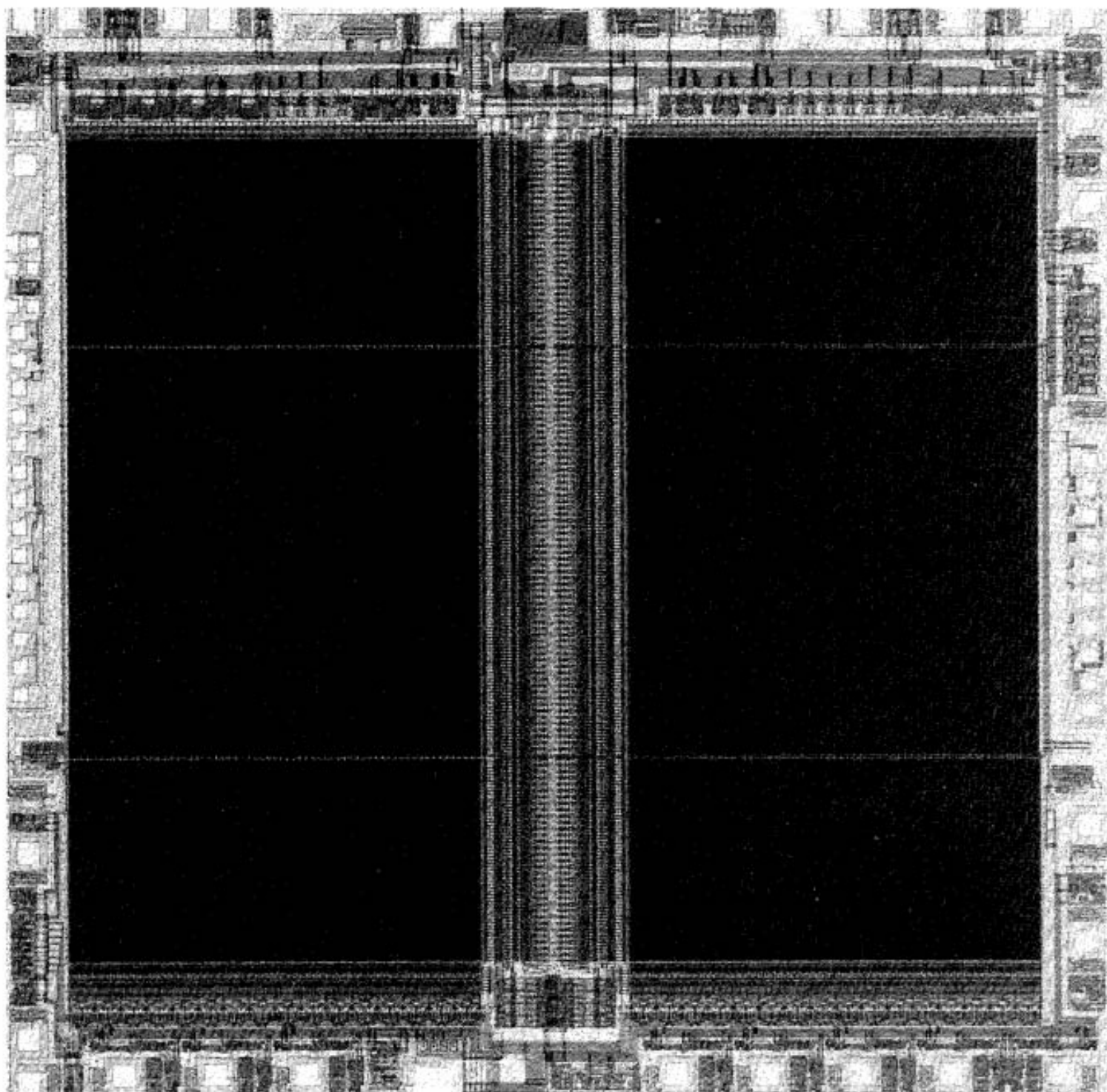


FIRST FLASH EEPROM MEMORY

ISSCC 1985



A 256K Flash EEPROM using Triple Polysilicon Technology

MASUOKA (TOSHIBA) AND his colleagues described a 256K flash EEPROM memory in 1985. The cells were programmed by channel hot electron injection and the erase was achieved by poly to poly field emission. A cell size of $64 \mu\text{m}^2$ and a die size of 5.7 mm x 5.8 mm was presented. This was early pioneering work for the modern flash memories.

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